

# Automotive Dual N-Channel 12 V (D-S) 175 °C MOSFETs

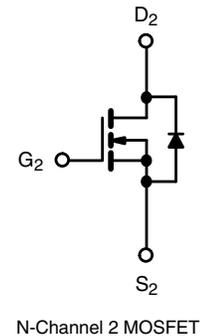
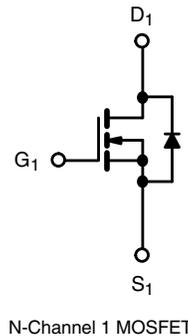
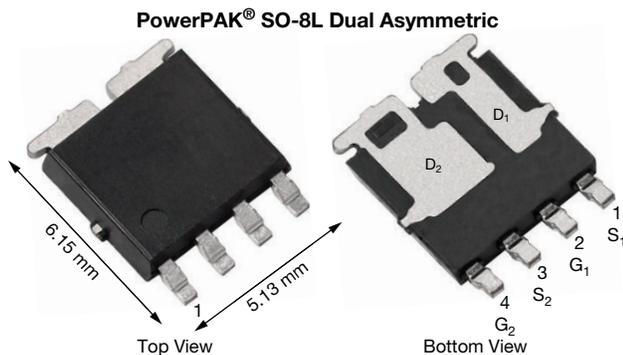


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

PRODUCT SUMMARY		
	N-CHANNEL 1	N-CHANNEL 2
$V_{DS}$ (V)	12	12
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10$ V	0.0065	0.0033
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5$ V	0.0093	0.0045
$I_D$ (A)	20	60
Configuration	Dual N	
Package	PowerPAK® SO-8L Dual Asymmetric	

## FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Drain-Source Voltage	$V_{DS}$	12	12	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current <sup>a</sup>	$I_D$	$T_C = 25$ °C	20	A
		$T_C = 125$ °C	20	
Continuous Source Current (Diode Conduction)	$I_S$	20 <sup>a</sup>	44	A
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	80	180	
Single Pulse Avalanche Current	$I_{AS}$	L = 0.1 mH	18	mJ
Single Pulse Avalanche Energy			$E_{AS}$	
Maximum Power Dissipation <sup>b</sup>	$P_D$	$T_C = 25$ °C	27	W
		$T_C = 125$ °C	9	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +175		°C
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL 1	N-CHANNEL 2	UNIT
Junction-to-Ambient	$R_{thJA}$	85	85	°C/W
Junction-to-Case (Drain)				

## Notes

- Package limited.
- Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.
- When mounted on 1" square PCB (FR4 material).
- Parametric verification ongoing.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



<b>SPECIFICATIONS</b> ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS			MIN.	TYP.	MAX.	UNIT
<b>Static</b>								
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	12	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	12	-	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 1	1	1.5	2	
		$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		N-Ch 2	1	1.5	2	
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		N-Ch 1	-	-	$\pm 100$	nA
				N-Ch 2	-	-	$\pm 100$	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}$	N-Ch 1	-	-	1	$\mu\text{A}$
		$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}$	N-Ch 2	-	-	1	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	-	50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	-	500	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 12\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	-	500	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 1	20	-	-	A
		$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch 2	30	-	-	
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 15\text{ A}$	N-Ch 1	-	0.0052	0.0065	$\Omega$
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}$	N-Ch 2	-	0.0025	0.0033	
		$V_{GS} = 10\text{ V}$	$I_D = 15\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 1	-	0.0075	-	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch 2	-	0.0031	-	
		$V_{GS} = 10\text{ V}$	$I_D = 15\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 1	-	0.0085	-	
		$V_{GS} = 10\text{ V}$	$I_D = 20\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch 2	-	0.0038	-	
		$V_{GS} = 4.5\text{ V}$	$I_D = 13\text{ A}$	N-Ch 1	-	0.0075	0.0093	
		$V_{GS} = 4.5\text{ V}$	$I_D = 18\text{ A}$	N-Ch 2	-	0.0034	0.0045	
Forward Transconductance <sup>b</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 15\text{ A}$		N-Ch 1	-	49	-	S
		$V_{DS} = 10\text{ V}, I_D = 20\text{ A}$		N-Ch 2	-	91	-	
<b>Dynamic <sup>b</sup></b>								
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	777	975	pF
		$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	2018	2525	
Output Capacitance	$C_{oss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	539	675	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	1313	1645	
Reverse Transfer Capacitance	$C_{rss}$	$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 1	-	270	340	
		$V_{GS} = 0\text{ V}$	$V_{DS} = 6\text{ V}, f = 1\text{ MHz}$	N-Ch 2	-	683	855	
Total Gate Charge <sup>c</sup>	$Q_g$	$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 20\text{ A}$	N-Ch 1	-	14.5	22	nC
		$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 60\text{ A}$	N-Ch 2	-	35.9	54	
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 20\text{ A}$	N-Ch 1	-	1.7	-	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 60\text{ A}$	N-Ch 2	-	4.1	-	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 20\text{ A}$	N-Ch 1	-	2.1	-	
		$V_{GS} = 10\text{ V}$	$V_{DS} = 6\text{ V}, I_D = 60\text{ A}$	N-Ch 2	-	4.3	-	
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		N-Ch 1	1.3	2.6	4	$\Omega$
				N-Ch 2	0.5	1.1	1.7	

**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.



SPECIFICATIONS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Turn-On Delay Time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 6\text{ V}$ , $R_L = 0.3\ \Omega$ $I_D \cong 20\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 1	-	8.8	13.5	ns
		$V_{DD} = 6\text{ V}$ , $R_L = 0.1\ \Omega$ $I_D \cong 60\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 2	-	10.7	16.5	
Rise Time <sup>c</sup>	$t_r$	$V_{DD} = 6\text{ V}$ , $R_L = 0.3\ \Omega$ $I_D \cong 20\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 1	-	3.2	5	
		$V_{DD} = 6\text{ V}$ , $R_L = 0.1\ \Omega$ $I_D \cong 60\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 2	-	4.5	7	
Turn-Off Delay Time <sup>c</sup>	$t_{d(off)}$	$V_{DD} = 6\text{ V}$ , $R_L = 0.3\ \Omega$ $I_D \cong 20\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 1	-	20	30	
		$V_{DD} = 6\text{ V}$ , $R_L = 0.1\ \Omega$ $I_D \cong 60\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 2	-	28	42	
Fall Time <sup>c</sup>	$t_f$	$V_{DD} = 6\text{ V}$ , $R_L = 0.3\ \Omega$ $I_D \cong 20\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 1	-	2.6	4	
		$V_{DD} = 6\text{ V}$ , $R_L = 0.1\ \Omega$ $I_D \cong 60\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_g = 1\ \Omega$	N-Ch 2	-	5	8	
Source-Drain Diode Ratings and Characteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	$I_{SM}$		N-Ch 1	-	-	80	
			N-Ch 2	-	-	180	
Forward Voltage	$V_{SD}$	$I_F = 10\text{ A}$ , $V_{GS} = 0\text{ V}$	N-Ch 1	-	0.8	1.2	V
		$I_F = 20\text{ A}$ , $V_{GS} = 0\text{ V}$	N-Ch 2	-	0.8	1.2	

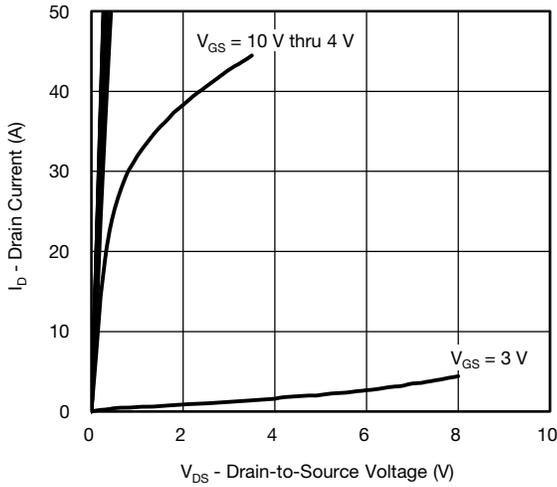
**Notes**

- a. Pulse test; pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.  
c. Independent of operating temperature.

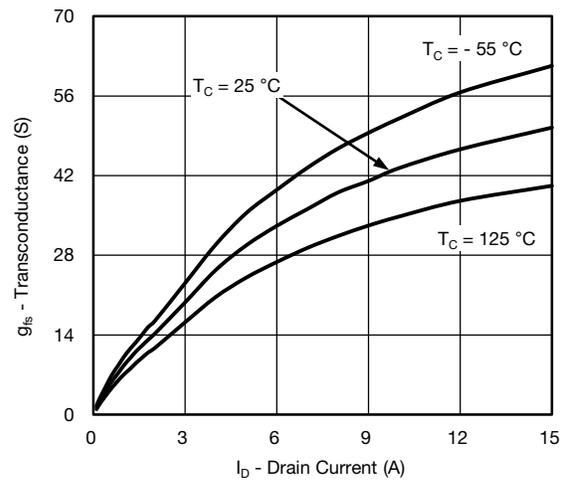
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



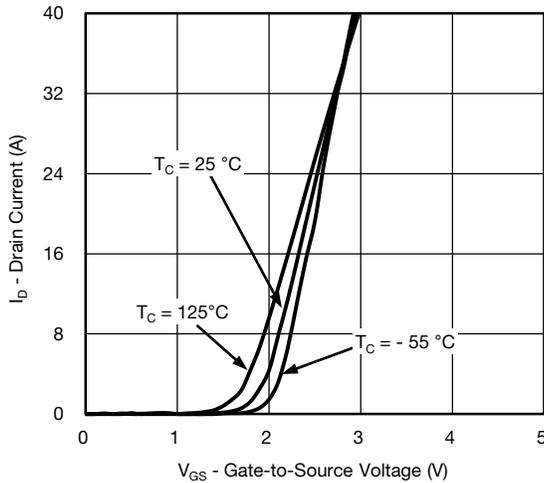
**N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



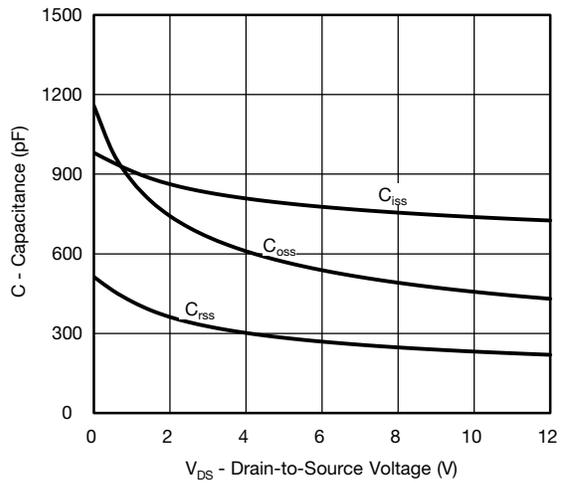
**Output Characteristics**



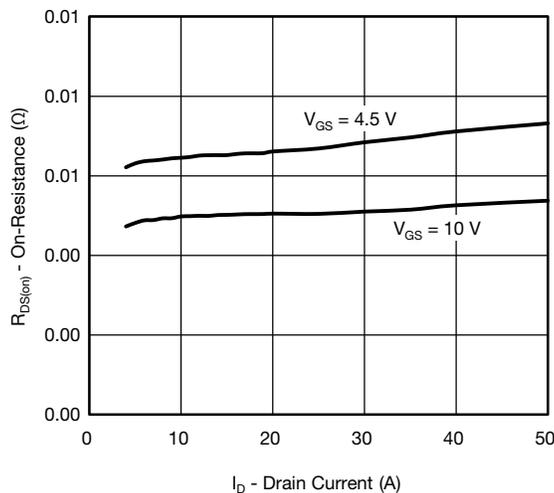
**Transconductance**



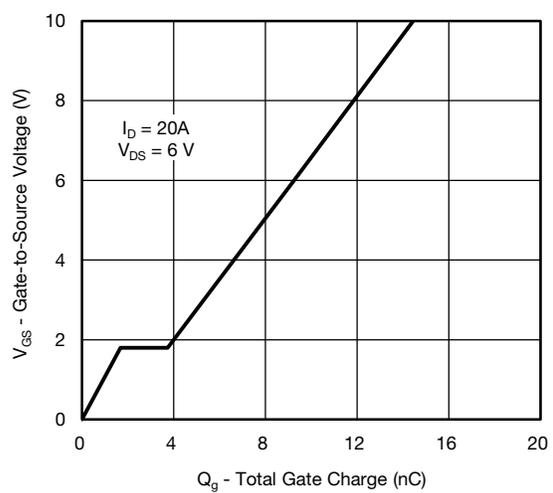
**Transfer Characteristics**



**Capacitance**

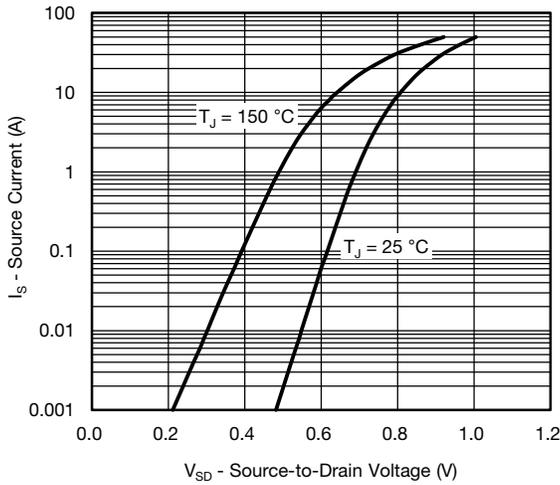


**On-Resistance vs. Drain Current**

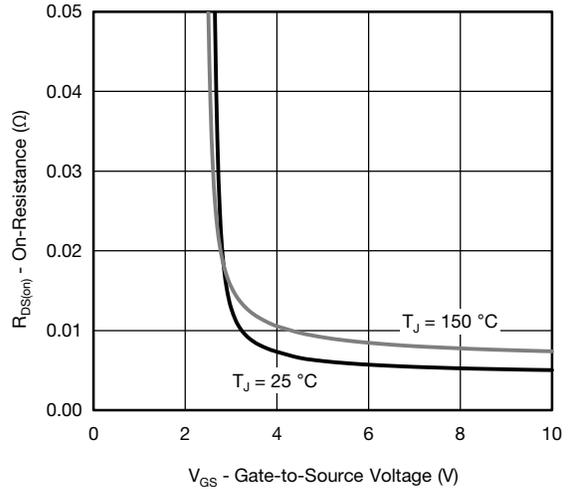


**Gate Charge**

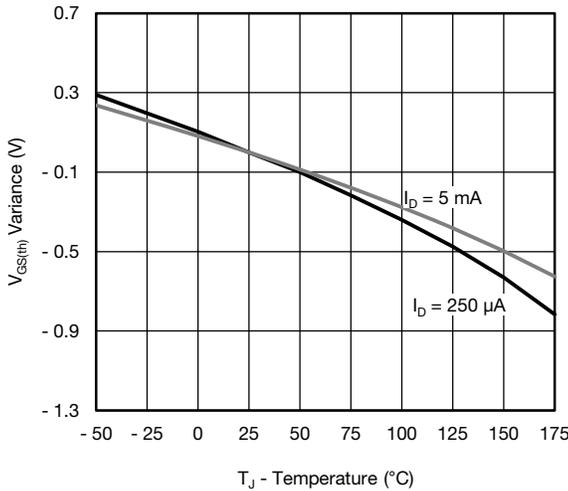
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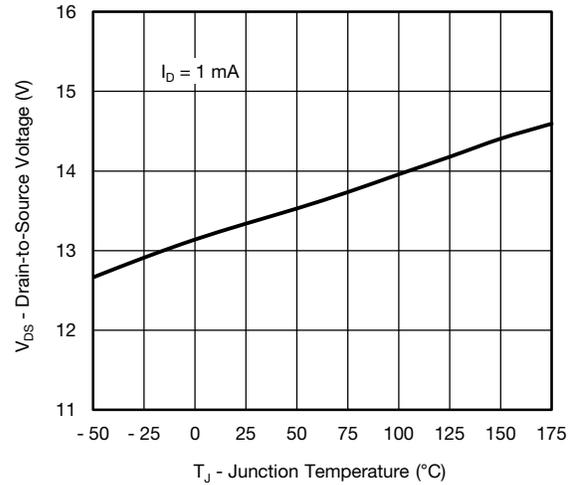
**Source Drain Diode Forward Voltage**



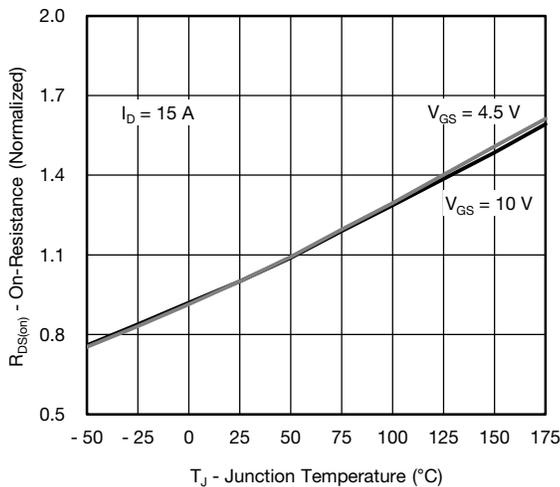
**On-Resistance vs. Gate-to-Source Voltage**



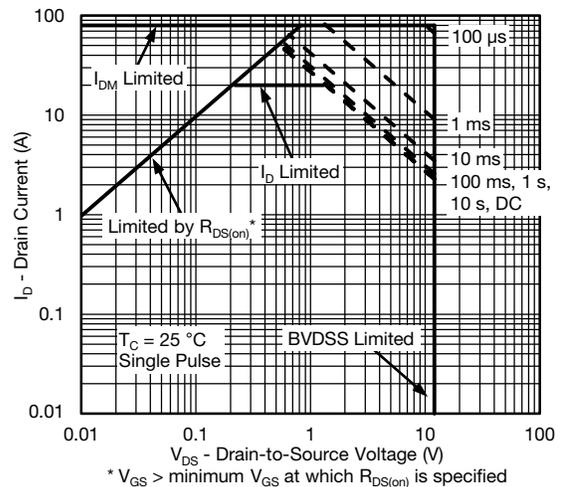
**Threshold Voltage**



**Drain Source Breakdown vs. Junction Temperature**



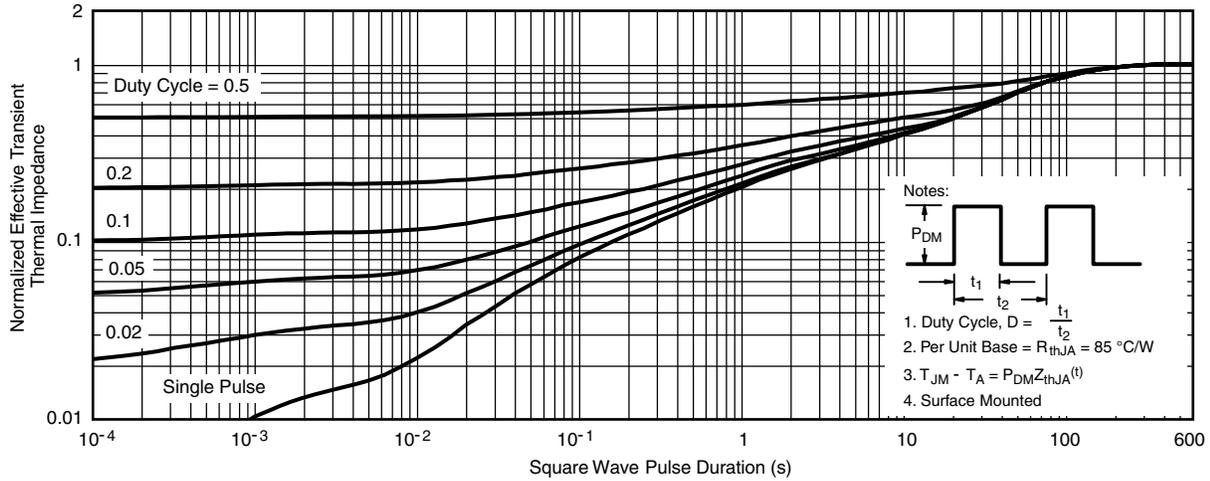
**On-Resistance vs. Junction Temperature**



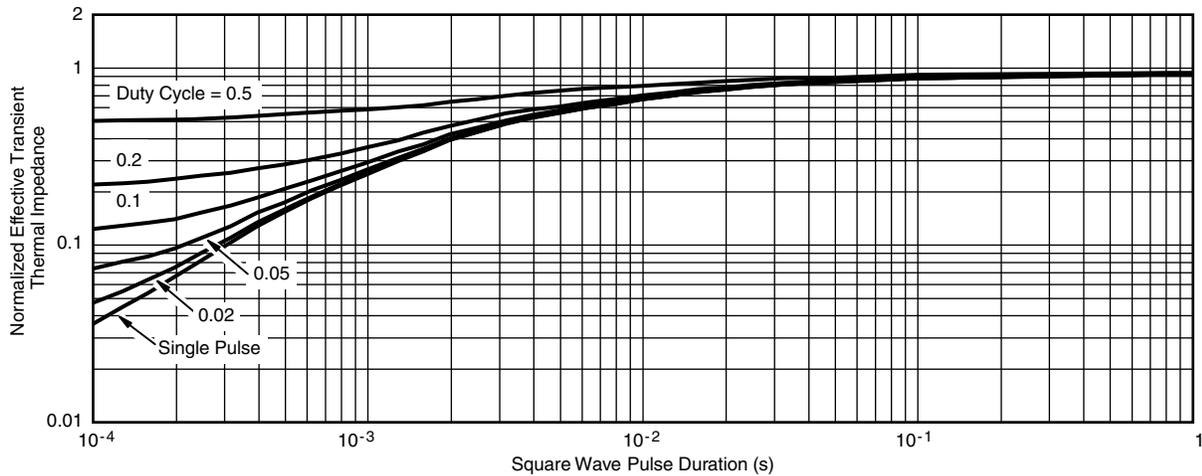
**Safe Operating Area**



**N-CHANNEL 1 TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

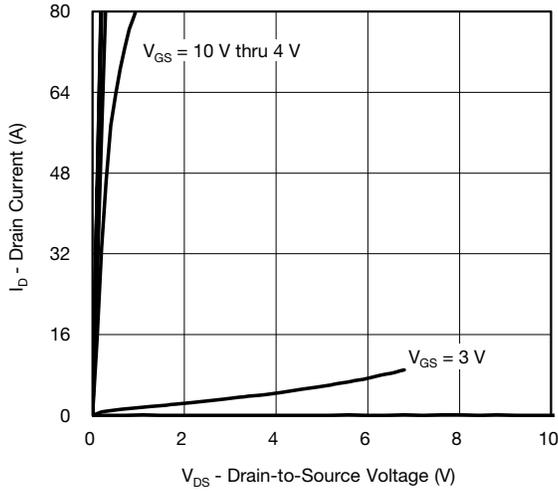


**Normalized Thermal Transient Impedance, Junction-to-Case**

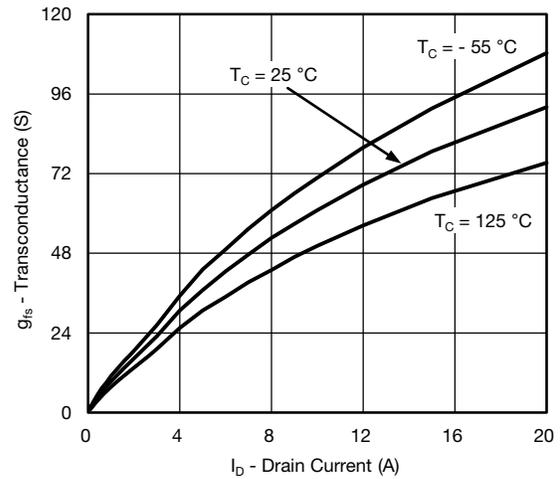
**Note**

- The characteristics shown in the graph:
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ ) is given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

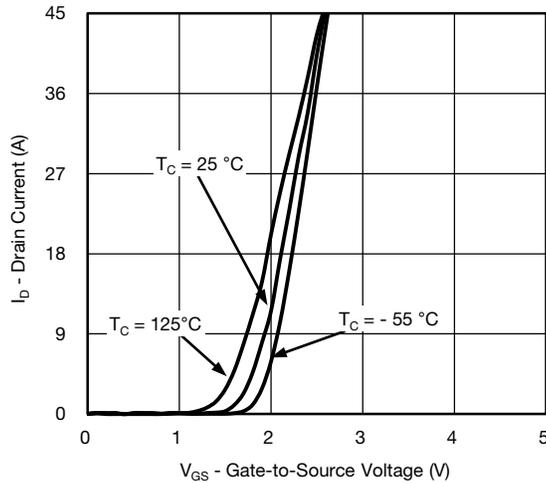
**N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



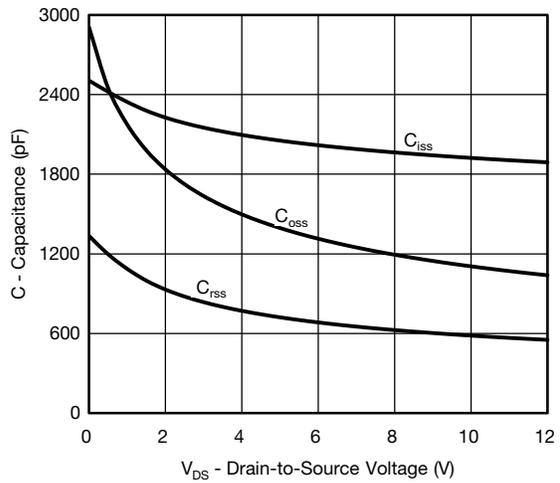
**Output Characteristics**



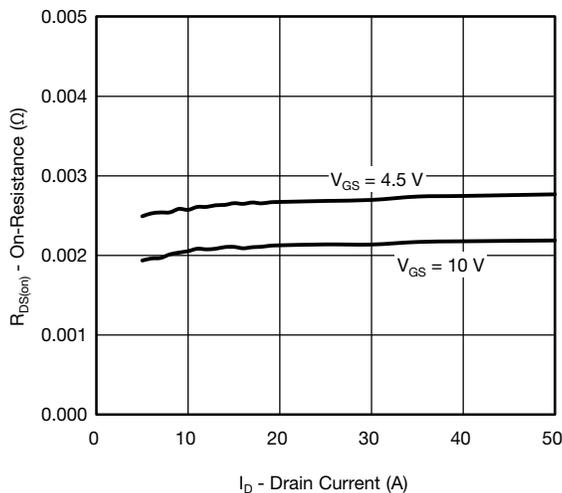
**Transconductance**



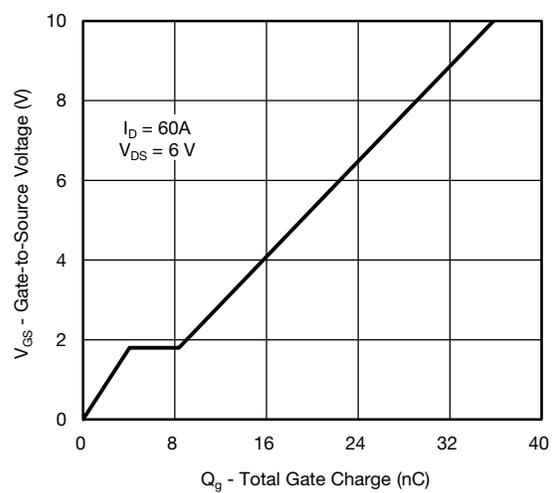
**Transfer Characteristics**



**Capacitance**



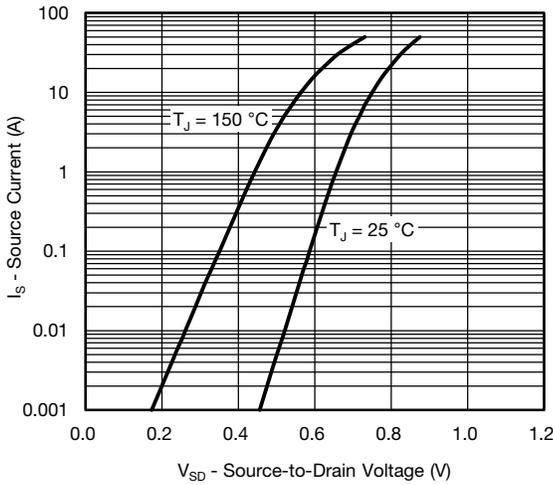
**On-Resistance vs. Drain Current**



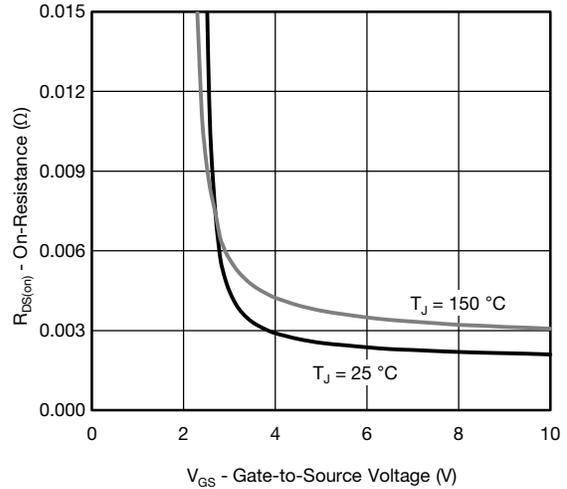
**Gate Charge**



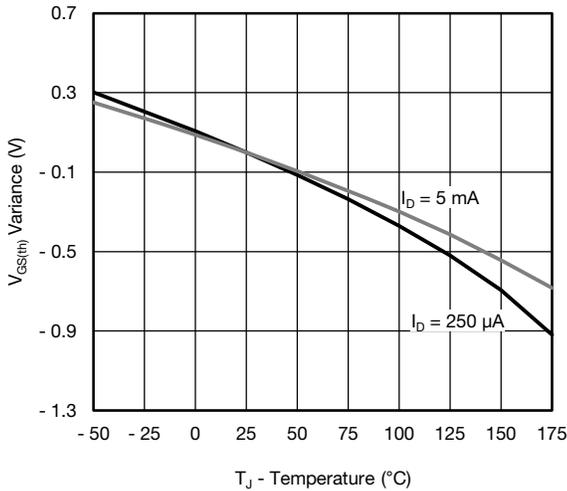
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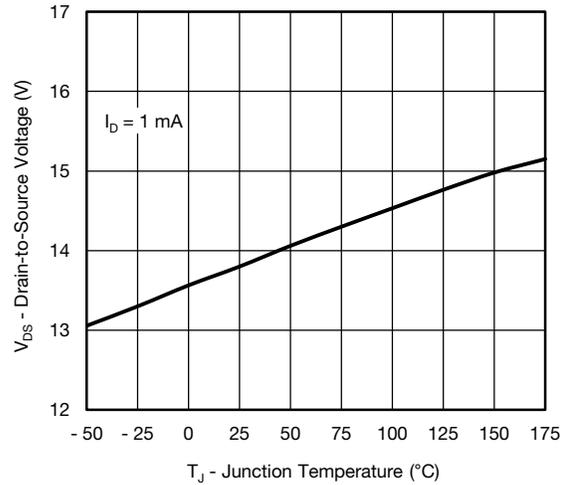
**Source Drain Diode Forward Voltage**



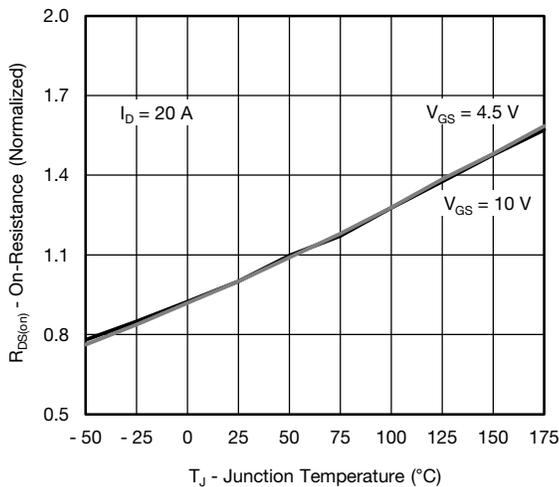
**On-Resistance vs. Gate-to-Source Voltage**



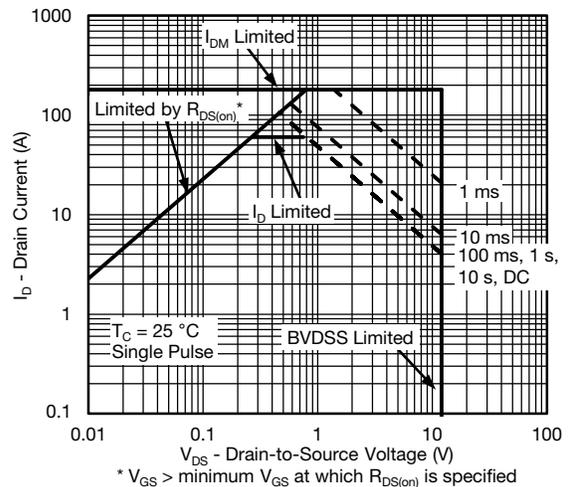
**Threshold Voltage**



**Drain Source Breakdown vs. Junction Temperature**

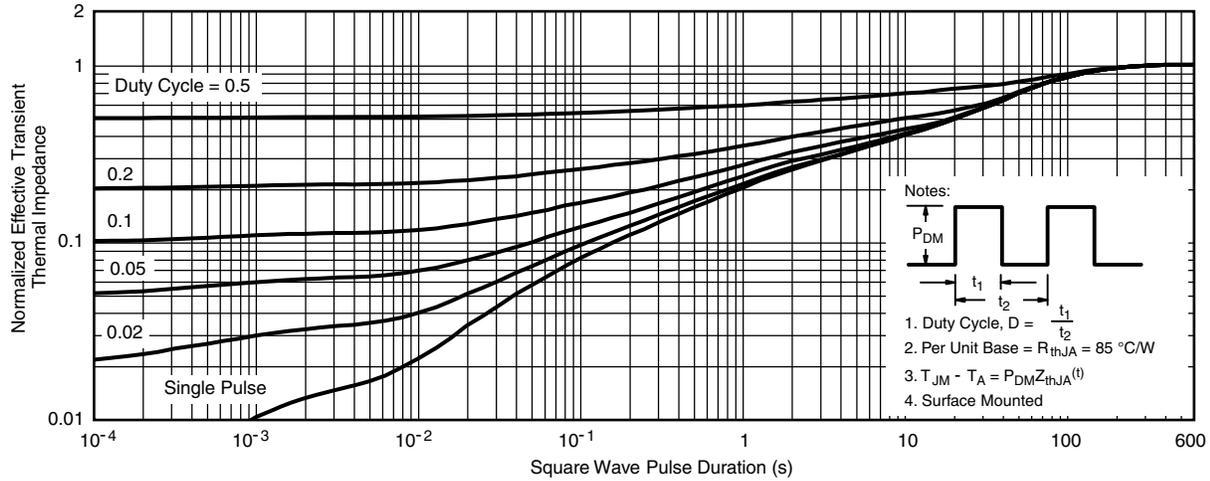


**On-Resistance vs. Junction Temperature**

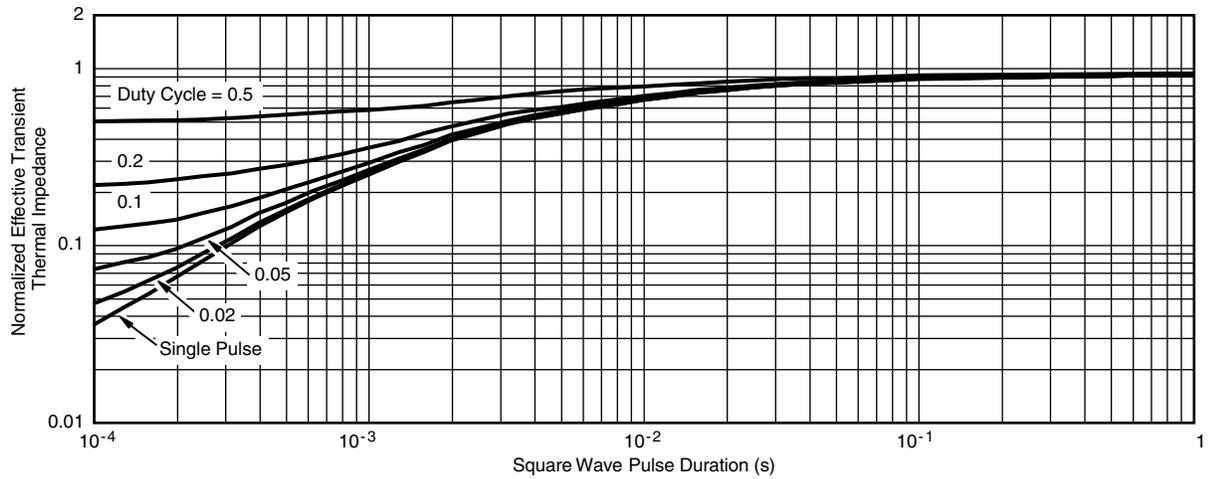


**Safe Operating Area**

**N-CHANNEL 2 TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the graph:
  - Normalized Transient Thermal Impedance Junction-to-Ambient ( $25\text{ }^\circ\text{C}$ ) is given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size  $1\text{ }'' \times 1\text{ }'' \times 0.062\text{ }''$ , double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?62926](http://www.vishay.com/ppg?62926).



PowerPAK® SO-8L

Ordering codes for the SQ rugged series power MOSFETs in the PowerPAK SO-8L package:

DATASHEET PART NUMBER	OLD ORDERING CODE <sup>a</sup>	NEW ORDERING CODE
SQJ200EP	-	SQJ200EP-T1_GE3
SQJ202EP	-	SQJ202EP-T1_GE3
SQJ401EP	SQJ401EP-T1-GE3	SQJ401EP-T1_GE3
SQJ402EP	SQJ402EP-T1-GE3	SQJ402EP-T1_GE3
SQJ403EEP	SQJ403EEP-T1-GE3	SQJ403EEP-T1_GE3
SQJ403EP	-	SQJ403EP-T1_GE3
SQJ410EP	SQJ410EP-T1-GE3	SQJ410EP-T1_GE3
SQJ412EP	SQJ412EP-T1-GE3	SQJ412EP-T1_GE3
SQJ422EP	SQJ422EP-T1-GE3	SQJ422EP-T1_GE3
SQJ431EP	SQJ431EP-T1-GE3	SQJ431EP-T1_GE3
SQJ443EP	SQJ443EP-T1-GE3	SQJ443EP-T1_GE3
SQJ446EP	-	SQJ446EP-T1_GE3
SQJ456EP	SQJ456EP-T1-GE3	SQJ456EP-T1_GE3
SQJ459EP	-	SQJ459EP-T1_GE3
SQJ460AEP	-	SQJ460AEP-T1_GE3
SQJ461EP	SQJ461EP-T1-GE3	SQJ461EP-T1_GE3
SQJ463EP	SQJ463EP-T1-GE3	SQJ463EP-T1_GE3
SQJ465EP	SQJ465EP-T1-GE3	SQJ465EP-T1_GE3
SQJ469EP	SQJ469EP-T1-GE3	SQJ469EP-T1_GE3
SQJ486EP	SQJ486EP-T1-GE3	SQJ486EP-T1_GE3
SQJ488EP	SQJ488EP-T1-GE3	SQJ488EP-T1_GE3
SQJ500AEP	SQJ500AEP-T1-GE3	SQJ500AEP-T1_GE3
SQJ840EP	SQJ840EP-T1-GE3	SQJ840EP-T1_GE3
SQJ844AEP	SQJ844AEP-T1-GE3	SQJ844AEP-T1_GE3
SQJ850EP	SQJ850EP-T1-GE3	SQJ850EP-T1_GE3
SQJ858AEP	SQJ858AEP-T1-GE3	SQJ858AEP-T1_GE3
SQJ886EP	SQJ886EP-T1-GE3	SQJ886EP-T1_GE3
SQJ910AEP	SQJ910AEP-T1-GE3	SQJ910AEP-T1_GE3
SQJ912AEP	SQJ912AEP-T1-GE3	SQJ912AEP-T1_GE3
SQJ940EP	SQJ940EP-T1-GE3	SQJ940EP-T1_GE3
SQJ942EP	SQJ942EP-T1-GE3	SQJ942EP-T1_GE3
SQJ951EP	SQJ951EP-T1-GE3	SQJ951EP-T1_GE3
SQJ952EP	-	SQJ952EP-T1_GE3
SQJ956EP	SQJ956EP-T1-GE3	SQJ956EP-T1_GE3
SQJ960EP	SQJ960EP-T1-GE3	SQJ960EP-T1_GE3
SQJ963EP	SQJ963EP-T1-GE3	SQJ963EP-T1_GE3
SQJ968EP	SQJ968EP-T1-GE3	SQJ968EP-T1_GE3
SQJ980AEP	SQJ980AEP-T1-GE3	SQJ980AEP-T1_GE3
SQJ992EP	SQJ992EP-T1-GE3	SQJ992EP-T1_GE3

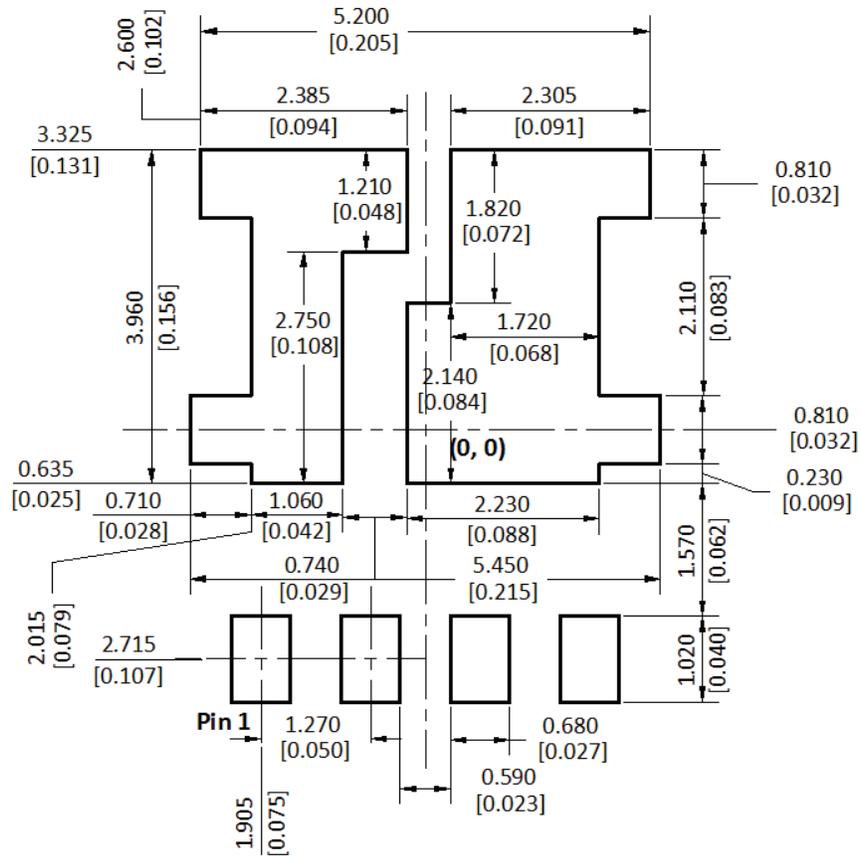
Note

a. Old ordering code is obsolete and no longer valid for new orders





## RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8L DUAL ASYMMETRIC



Recommended Minimum Pads  
Dimensions in mm [inches]



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**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



#### Как с нами связаться

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